



## LIGHT-EMITTERS WITH GROUP III-NITRIDE-BASED QUANTUM WELL ACTIVE REGIONS HAVING GAN INTERLAYERS

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### The Invention

UW-Madison researchers have developed a group III-nitride-based light emitting devices for efficient LED and laser applications. These devices have one or more quantum wells in the active region with a double well design using an AlInGa<sub>N</sub> alloy or an InGa<sub>N</sub> alloy adjacent to GaN interlayer, both of which are disposed between two barrier layers of an AlGa<sub>N</sub> alloy or low-In-content AlInGa<sub>N</sub> alloy.

#### Tech Fields

- [Semiconductors & Integrated Circuits : Components & materials](#)

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